

Features

- Low capacitance: 0.4pF typical (I/O to I/O)
- Ultra low leakage: nA level
- Low operating voltage: 5V
- Low clamping voltage
- Up to 4 lines and one power line protects
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
Air discharge: ±18kV
Contact discharge: ±15kV
 - IEC61000-4-4 (EFT) 40A (5/50ns)
 - IEC61000-4-5 (Lightning) 5A (8/20µs)
- RoHS Compliant

Description

The ESD0541L7 is a low capacitance TVS array,utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The ESD0541L7 complies with the IEC 61000-4-2 (ESD) standard with ±15kV air and ±8kV contact discharge. It is assembled into a 6-pin DFN1616-6 lead-free package. The leads are finished with NiPdAu. Each device will protect up to four high-speed lines. The combination of small size, low capacitance, and high surge capability makes them ideal for use in applications such as cellular phones, LCD displays, USB, and multi media card interfaces.

Mechanical Characteristics

- Package: DFN1616-6
- Lead Finish: NiPdAu
- Case Material: “Green” Molding Compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram

Applications

- USB 2.0 and USB OTG
- Multi Media Card Interfaces
- SD Card Interfaces
- MDDI Ports
- SIM Ports

Part Number Code

E	S	D	0	5	1	1	L	1
1	2	3	4	5	6	7	8	9

Product Type	
ESD	TSK Electrostatic suppressor ESD Type

Reverse Working Voltage (V)	
3V3	3.3V
05	5V
16	16V

Line	
1	1-Line
2	2-Line
3	3-Line

Capacitance Type	
L	Low
X	Normal

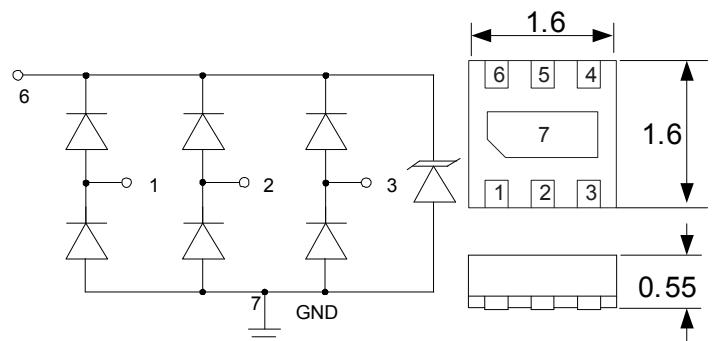
directional	
0	Bi
1	Uni

Size	
1	0201
2	0402
3	DFN0603
4	DFN1006

★ Code 4 to 9 is optional



Dimensions and Pin Configuration



Circuit Diagram

Pin Schematic

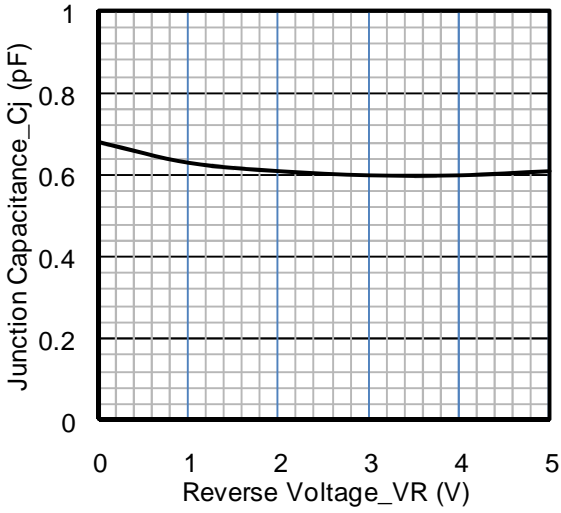
Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	100	W
Peak Pulse Current (8/20 μs)	I _{PP}	5	A
ESD per IEC 61000-4-2 (Air)	V _{ESD}	± 18	kV
ESD per IEC 61000-4-2 (Contact)		± 15	
Operating Temperature Range	T _J	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	T _{stg}	-55 to +150	$^{\circ}\text{C}$

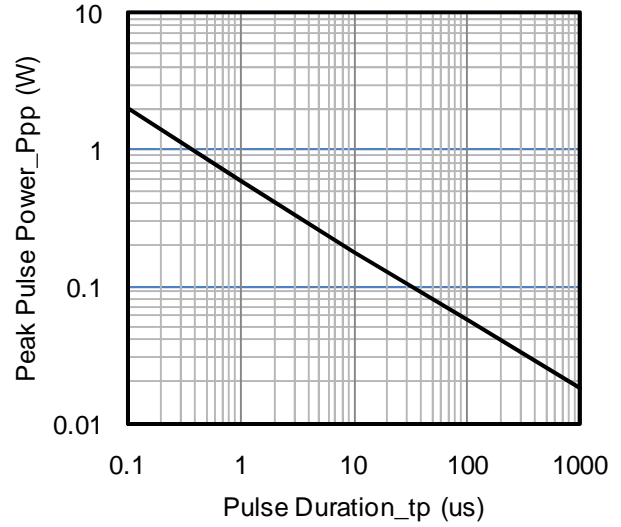
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			5	V	Pin 6 to ground
Breakdown Voltage	V _{BR}	6			V	I _T = 1mA, pin 6 to ground
Reverse Leakage Current	I _R			0.5	μA	V _{RWM} = 5V, pin 6 to ground
Clamping Voltage	V _C			10	V	I _{PP} = 1A (8 x 20 μs pulse), any I/O pin to ground
Clamping Voltage	V _C			20	V	I _{PP} = 5A (8 x 20 μs pulse), any I/O pin to ground
Junction Capacitance	C _J			0.4	pF	V _R = 0V, f = 1MHz, between I/O pins
Junction Capacitance	C _J			0.8	pF	V _R = 0V, f = 1MHz, any I/O pin to ground

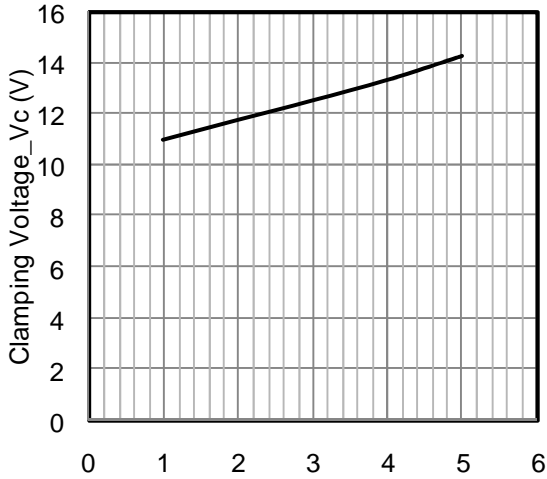
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



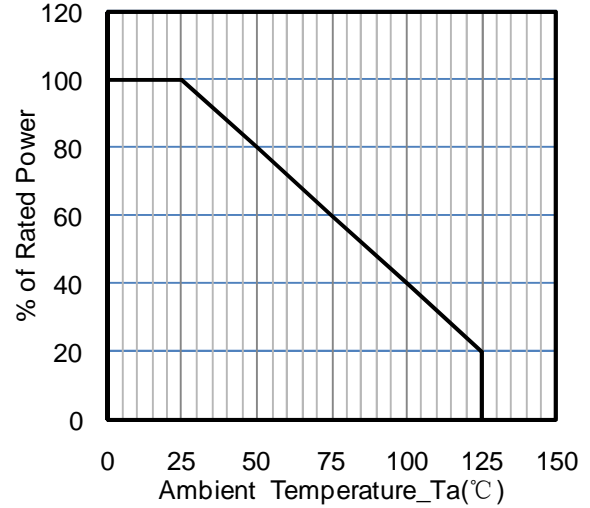
Junction Capacitance vs. Reverse Voltage



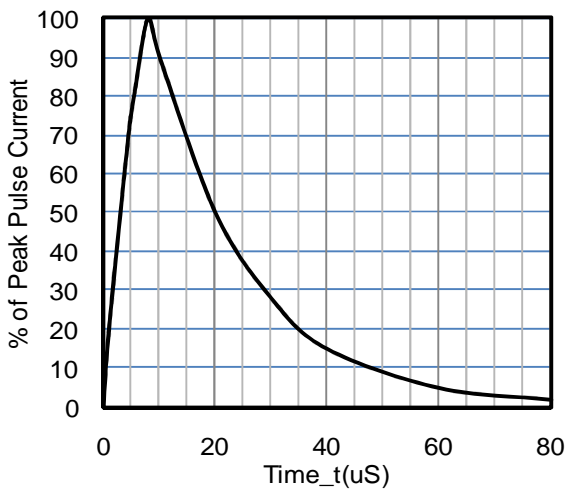
Peak Pulse Power vs. Pulse Time



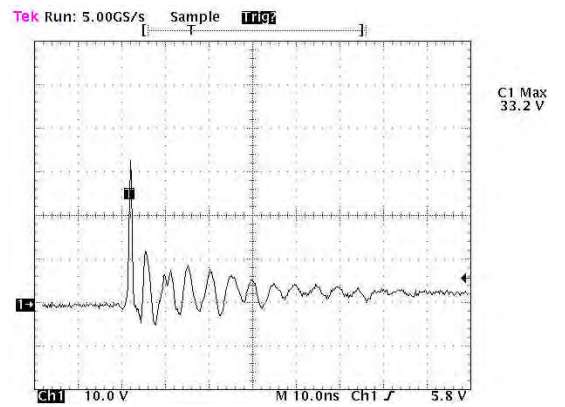
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



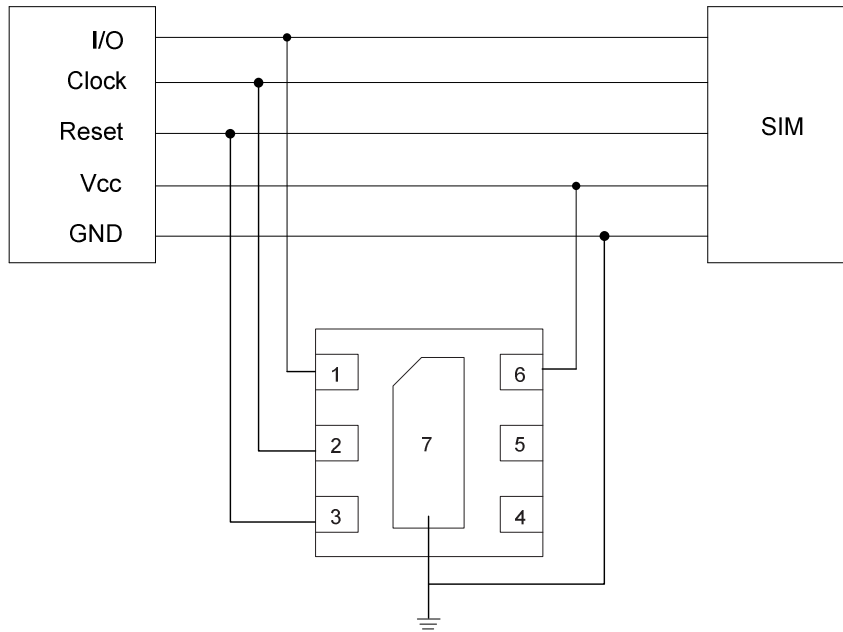
8 X 20us Pulse Waveform



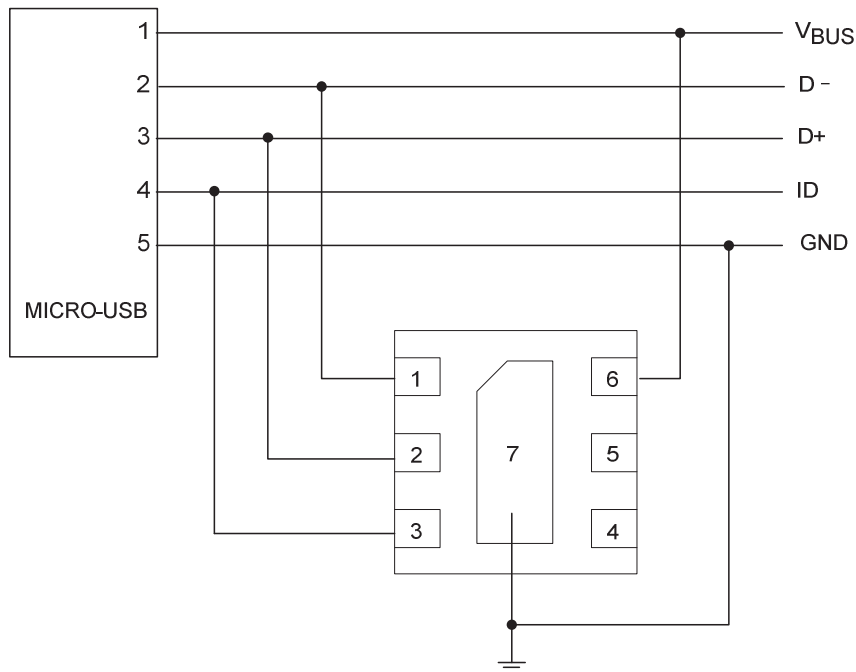
ESD Clamping Voltage

8 kV Contact per IEC61000-4-2

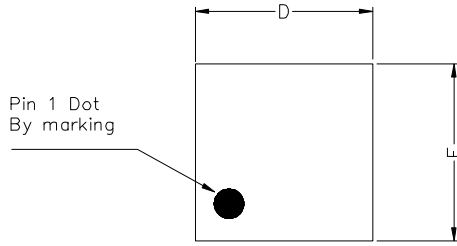
ESD0541L7 on SIM Port Application



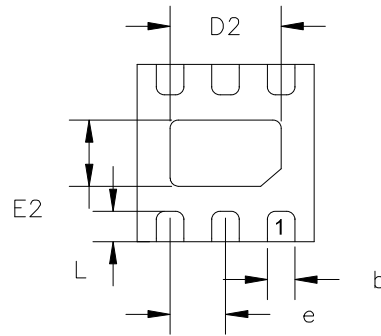
ESD0541L7 on USB Port Application



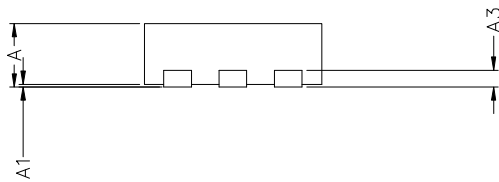
DFN1616-6 Package Outline Drawing



TOP VIEW



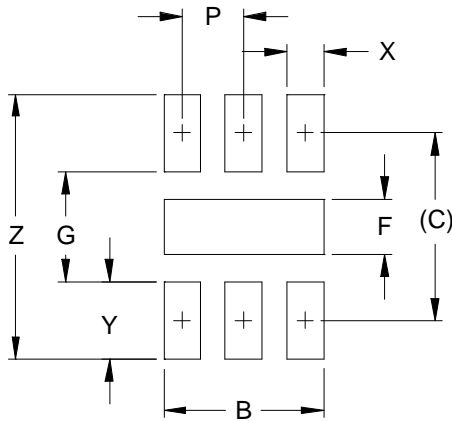
BOTTOM VIEW



SIDE VIEW

COMMON DIMENSIONS(MM)			
PKG. REF.	UT:ULTRA THIN		
	MIN.	NOM.	MAX.
A	0.50	0.55	0.60
A1	0.00	-	0.05
A3	0.15 REF.		
D	1.55	1.60	1.65
E	1.55	1.60	1.65
D2	0.90	1.00	1.05
E2	0.50	0.60	0.65
L	0.20	0.25	0.30
b	0.20	0.25	0.30
e	0.50 BSC		

Suggested Land Pattern



DIMENSIONS		
DIM	INCHES	MILLIMETERS
B	.051	1.30
C	.060	1.52
P	.020	0.50
F	.018	0.45
G	.035	0.89
X	.012	0.30
Y	.025	0.63
Z	.085	2.15

Ordering Information

Part Number	Packaging	Reel Size
ESD0541L7	3000/Tape & Reel	7 inch